TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRIAC

TLP3051(S),TLP3052(S)

OFFICE MACHINE
HOUSEHOLD USE EQUIPMENT
TRIAC DRIVERSOLID STATE RELAY

The TOSHIBA TLP3051(S) and TLP3052(S) consists of a photo-triac optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package.

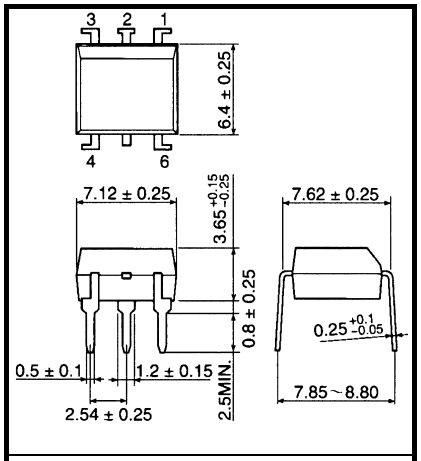
- Peak Off-State Voltage : 600V(Min)
- Trigger LED Current : 15mA(Max) (TLP3051(S))
  10mA(Max) (TLP3052(S))
- On-State Current : 100mA(Max)
- Isolation Voltage : 5000Vrms(Min)
- UL Recognized : UL1577,File No.E67349
- SEMKO Approved : SS EN60065
  SS EN60950, File No.9841111
- BSI Approved : BS EN60065, File No.8385
  BS EN60950, File No.8386
- Option (D4) type
  VDE approved: DIN EN60747-5-2
  Approved No. 40009302
  Maximum operating insulation voltage: 890V_{PK}
  Highest permissible over voltage: 8000V_{PK}

  (Note):When a EN60747-5-2 approved type is needed,
  please designate the "Option (D4)"

- Construction Mechanical Rating

	7.62 mm pich Standard Type	10.16 mm pich TLPxxxxF Type
Creepage Distance	7.0 mm (Min)	8.0 mm (Min)
Clearance	7.0 mm (Min)	8.0 mm (Min)
Insulation Thickness	0.5 mm (Min)	0.5 mm (Min)

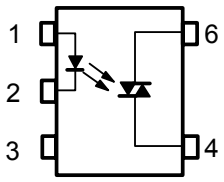
Unit in mm



JEDEC	
TOSHIBA	11-7A9

Weight: 0.39 g

Pin Configuration (top view)



1: Anode
2: Csthode
3: N.C.
4:Terminal 1
6:Terminal 2

Absolute Maximum Ratings (Ta=25°C)

	CHARACTERISTIC		SYMBOL	RATING	UNIT
LED	Forward Current		I_F	50	mA
	Forward Current Derating (Ta≥53°C)		ΔI_F /°C	−0.7	mA /°C
	Peak Forward Current (100μs pulse, 100pps)		I_{FP}	1	A
	Power Dissipation		P_D	100	mW
	Power Dissipation Derating (Ta≥25°C)		ΔP_D /°C	-1.0	mW/°C
	Reverse Voltage		V_R	5	V
	Junction Temperature		Tj	125	°C
DETECTOR	Off-State Output Terminal Voltage		V_{DRM}	600	V
	On-State RMS Current	Ta=25°C	$I_{T(RMS)}$	100	mA
		Ta=70°C		50	
	On-State Current Derating (Ta≥25°C)		ΔI_T/°C	-1.1	mA /°C
	Peak On-State Current (100μs pulse, 120pps)		I_{TP}	2	A
	Peak Nonrepetitive Surge Current (Pw=10ms,DC=10%)		I_{TSM}	1.2	A
	Power Dissipation		P_D	300	mW
	Power Dissipation Derating (Ta≥25°C)		ΔP_D /°C	-4.0	mW/°C
	Junction Temperature		T_j	115	°C
Storage Temperature Range			T_{stg}	−55~150	°C
Operating Temperature Range			T_{opr}	−40~100	°C
Lead Soldering Temperature (10s)			T_{sol}	260	°C
Total Package Power Dissipation			P_T	330	mW
Total Package Power Dissipation Derating (Ta≥25°C)			ΔP_T/°C	-4.4	mW /°C
Isolation Voltage (AC,1min. , R.H.≤60%) (Note 2)			BV_S	5000	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

(Note 2) Device considered a two terminal device :Pins1, 2 and 3 shorted together and pin 4 and pin 6 shorted together.

Recommended Operating Conditions

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V_{AC}	—	—	240	V_{ac}
Forward Current	I_F^*	15	20	25	mA
Peak On-State Current	I_{TP}	—	—	1	A
Operating Temperature	T_{opr}	−25	—	85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

*In The case of TLP3052

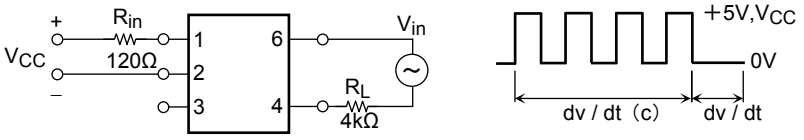
Individual Electrical Characteristics (Ta=25°C)

	CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	V_F	I_F = 10 mA	1.0	1.15	1.3	V
	Reverse Current	I_R	V_R = 5 V	—	—	10	μA
	Capacitance	C_T	V = 0, f=1MHz	—	30	—	pF
DETECTOR	Peak Off-State Current	I_{DRM}	V_{DRM}=600V	—	10	1000	nA
	Peak On-State Voltage	V_{TM}	I_{TM}=100mA	—	1.7	3.0	V
	Holding Current	I_H	—	—	1.0	—	mA
	Critical Rate of Rise of Off-State Voltage	dv/dt	Vin=240Vrms , Ta=85°C (Fig.1)	—	500	—	V/μs
	Critical Rate of Rise of Commutating Voltage	dv/dt(c)	Vin=60Vrms , IT=15mA (Fig.1)	—	0.2	—	V/μs

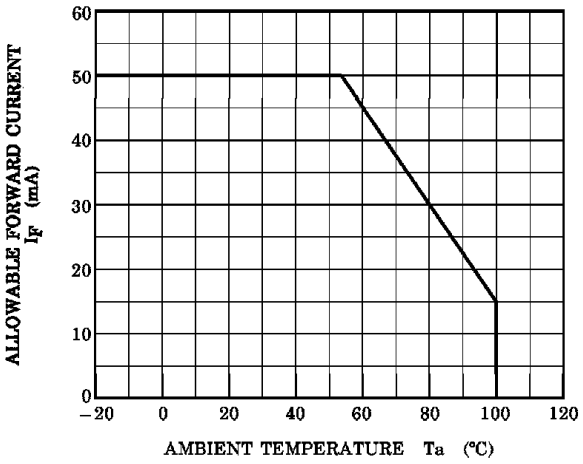
Coupled Electrical Characteristics (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Trigger LED Current	TLP3051(S)	I_{FT}	V_T=6V	—	—	15	mA
	TLP3052(S)			—	5	10	
Capacitance (Input to Output)		C_S	VS=0 , f=1MHz	—	0.8	—	pF
Isolation Resistance		R_S	VS=500V(R.H.≤60%)	5×10^{10}	10^{14}	—	Ω
Isolation Voltage		BV_S	AC , 1minute	5000	—	—	Vrms
			AC , 1second,in oil	—	10000	—	
			DC , 1minute,in oil	—	10000	—	Vdc

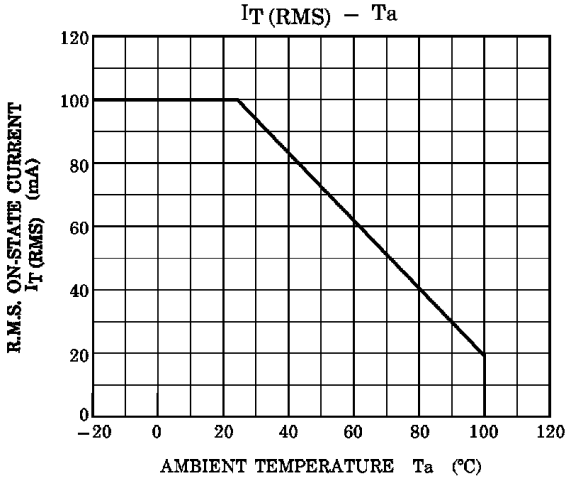
Fig. 1 dv / dt test circuit



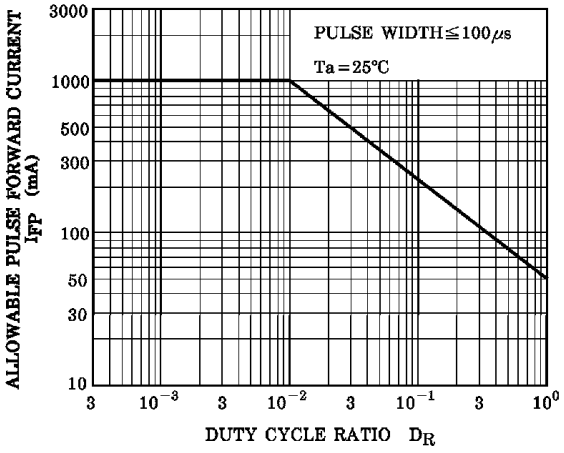
I_F – Ta



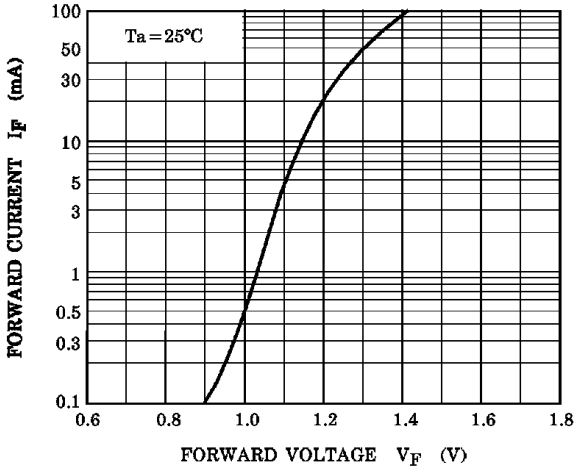
$I_{T\,(RMS)}$ – Ta



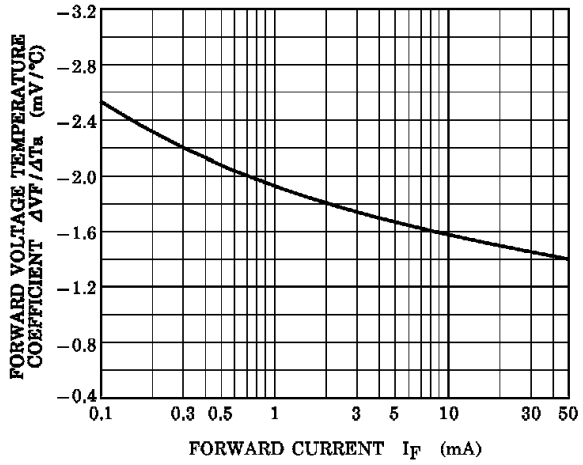
I_{FP} – D_R



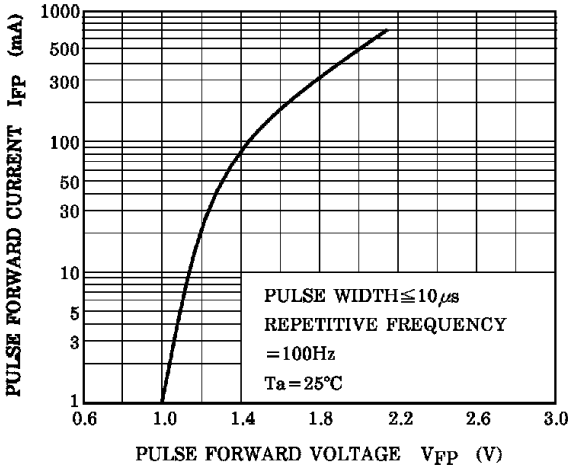
I_F – V_F



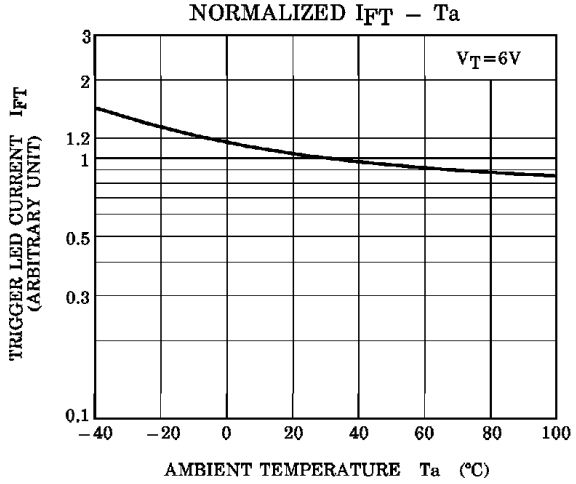
$\Delta V_F / \Delta Ta$ – I_F



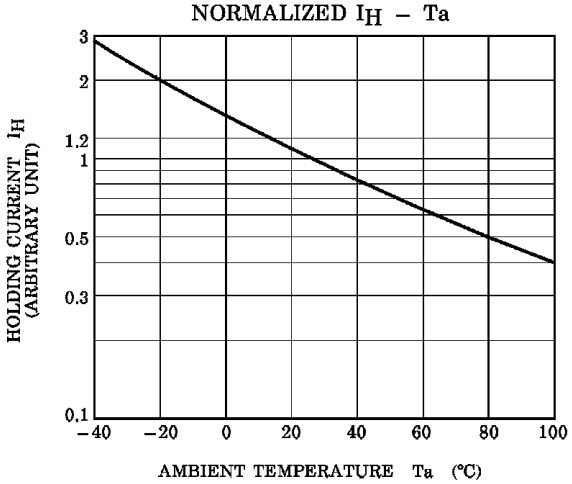
I_{FP} – V_{FP}



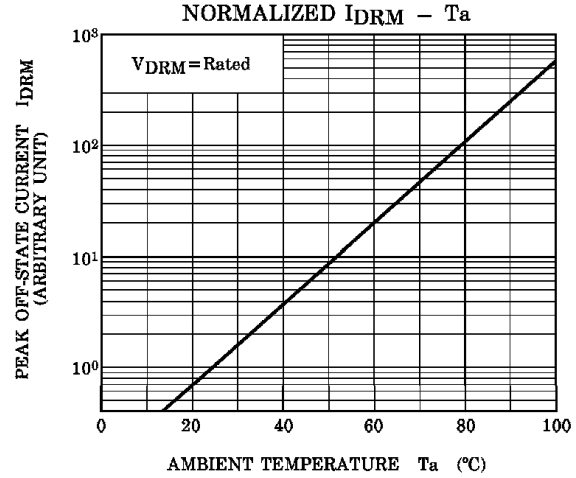
NORMALIZED I_{FT} – Ta



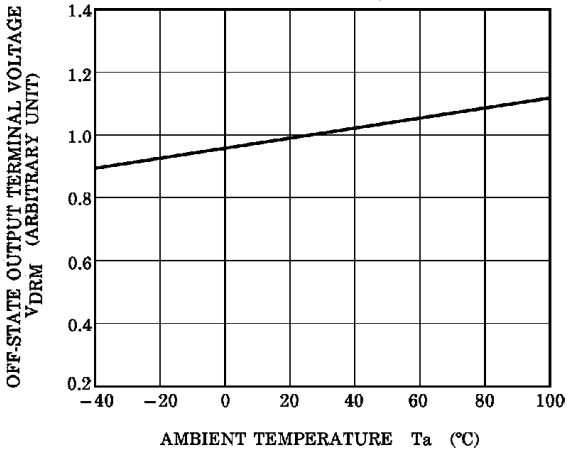
NORMALIZED I_H – Ta



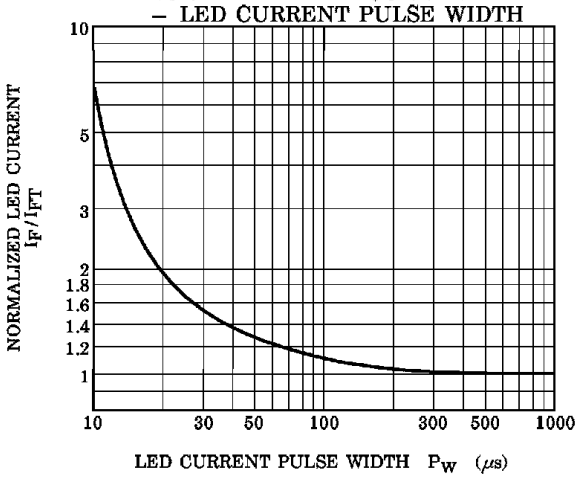
NORMALIZED I_{DRM} – Ta



NORMALIZED V_{DRM} – Ta



NORMALIZED LED CURRENT – LED CURRENT PULSE WIDTH



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